

K. Memory (Design & Process Technology) 분과

2017년 2월 14일 (화), 10:10-11:40
Room B (토파즈, 2층)

[TB2-K] Dielectric, Ferromagnetic, and Phase Change Materials For Memory Application

좌장: 이재구(삼성전자), 김윤(부산대학교)

TB2-K-1 10:10-10:25	Effect of ALD Growth Cycle for $\text{HfO}_2/\text{Al}_2\text{O}_3$ Multi-Stack on the Memory Characteristics in MAHAOS Structure Heedo Na, Juyoung Jeong, Tae Ho Kim, and Hyunchul Sohn <i>Department of Materials Science and Engineering, Yonsei University</i>
TB2-K-2 10:25-10:40	Power and Cost-effective Transmitter and Receiver Schemes of NAND Flash for Enterprise SSD Application Kwansu Shon, Yohan Jeong, Daehan Kwon, and Junhyun Chun <i>SK Hynix Inc.</i>
TB2-K-3 10:40-10:55	La_2O_3-capped SiO_2의 Effective Workfunction 거동 연구 김형철, 이승미, 조흥재, 장세역 <i>SK하이닉스 미래기술연구소</i>
TB2-K-4 10:55-11:10	Investigation on High Performance SONOS Flash Memory with Silicon Nanocrystals Embedded in Silicon Nitride Charge Trapping Layer Jae-Gab Lim ¹ , Seung-Dong Yang ¹ , Ho-Jin Yun ¹ , Jun-Kyo Jeong ¹ , Jung-Hyun Park ¹ , Yu-Jeong Kim ¹ , Chan Lim ² , Gyu-seok Cho ² , Seong-gye Park ² , Chul Huh ³ , Hi-Deok Lee ¹ , and Ga-Won Lee ¹ ¹ <i>Department of Electronics Engineering, Chungnam National University</i> , ² <i>SK Hynix Inc.</i> , ³ <i>Electronics and Telecommunications Research Institute</i>
TB2-K-5 11:10-11:25	Thermally Induced Magnetization Switching Behavior by Spin-Orbit-Torque in W/CoFeB/MgO Frames for STT-MRAM Application. SeungMo Yang ¹ , GwangGuk An ¹ , WooSeong Chung ³ , Haesoo Park ¹ , Wonbae Ko ¹ , and JinPyo Hong ^{1,2} ¹ <i>Novel Functional Materials and Devices Lab, The Research Institute for Natural Science, Department of Physics, Hanyang University</i> , ² <i>Division of Nano-Scale Semiconductor Engineering, Hanyang University</i> , ³ <i>Nano Quantum Electronics Lab, Department of Electronics and Computer Engineering, Hanyang University</i>
TB2-K-6 11:25-11:40	Design of In_3SbTe_2 Phase-Change Material with Local Distortion for Memory and Neuromorphic System Minho Choi ¹ , Heechae Choi ^{2,3} , Seungchul Kim ² , Yong Tae Kim ⁴ , and Jinho Ahn ¹ ¹ <i>Division of Materials Science and Engineering, Hanyang University</i> , ² <i>Center for Computational Science, Korea Institute of Science and Technology</i> , ³ <i>Virtual Lab Company</i> , ⁴ <i>Semiconductor Materials and Device Laboratory, Korea Institute of Science and Technology</i>